

**GaAs SPDT Switch
DC - 4 GHz**

**SW-226/227/228
V4**

Features

- Terminated (SW-226), High Isolation (SW-227), Low Loss (SW-228)
- Fast Switching Speed: 6 nS Typical
- Ultra Low DC Power Consumption
- Lead-Free 7-Lead Ceramic Package
- RoHS* Compliant and 260°C Reflow Compatible

Description

M/A-COM's SW-226/227/228 are GaAs MMIC SPDT switches packaged in lead-free, surface mount CR-2 ceramic style packages. The SW-226 is a terminated SPDT. The SW-227 offers high isolation. The SW-228 offers low insertion loss. This ceramic switch platform has a common footprint for all three designs. The CR-2 package is hermetically sealed, making these switches ideal for space, military radios, and other environmentally harsh applications.

Typical applications include synthesizer switching, transmit/receive switching, switch matrices and filter banks in systems such as radio and cellular equipment, PCM, GPS, and fiber optic modules.

The SW-226/227/228 are fabricated as monolithic GaAs MMICs using a 1.0 micron MESFET process.

Ordering Information

Part Number	Package
SW-226	Ceramic (CR-2)
SW-227	Ceramic (CR-2)
SW-228	Ceramic (CR-2)

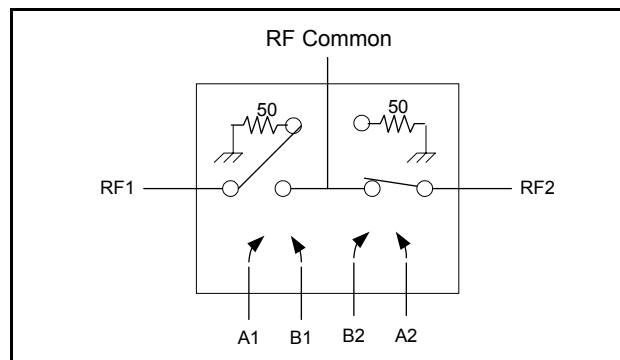
Absolute Maximum Ratings ^{1,2}

Parameter	Absolute Maximum
Input Power 0.05 GHz 0.5 - 4.0 GHz	+27 dBm +34 dBm
Control Voltage	-8.5 V ≤ Vc ≤ +5 V
Operating Temperature	-55°C to +125°C
Storage Temperature	-65°C to +150°C

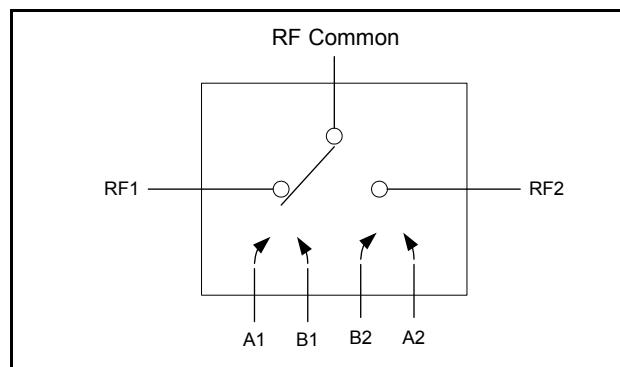
1. Exceeding any one or combination of these limits may cause permanent damage to this device.
2. M/A-COM does not recommend sustained operation near these survivability limits.

* Restrictions on Hazardous Substances, European Union Directive 2002/95/EC.

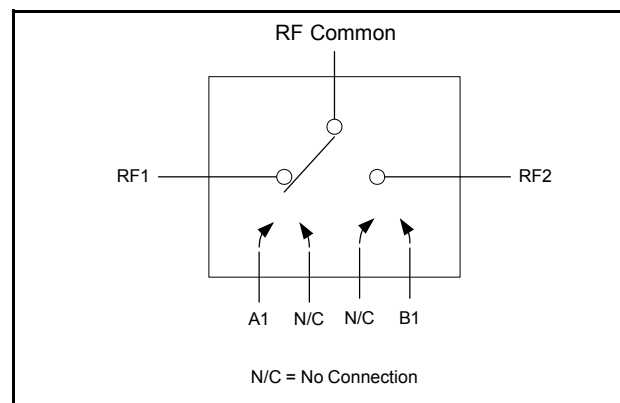
**Block Diagram/Pin Configuration
SW-226 ³**



**Block Diagram/Pin Configuration
SW-227 ³**



**Block Diagram/Pin Configuration
SW-228 ³**



3. Bottom of case is RF ground.

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Electrical Specifications: $T_A = -55^{\circ}\text{C}$ to $+85^{\circ}\text{C}$, $V_c = 0\text{ V} / -5\text{ V}$, $Z_0 = 50\ \Omega$ ⁴

Parameter	Test Conditions	Units	Min.	Typ.	Max.
Insertion Loss (SW-226)	DC - 0.5 GHz	dB	—	—	0.9
	DC - 1 GHz	dB	—	—	1.0
	DC - 2 GHz	dB	—	—	1.2
	DC - 4 GHz	dB	—	—	1.5
Insertion Loss (SW-227)	DC - 0.5 GHz	dB	—	—	0.9
	DC - 1 GHz	dB	—	—	1.0
	DC - 2 GHz	dB	—	—	1.1
	DC - 4 GHz	dB	—	—	1.4
Insertion Loss (SW-228)	DC - 0.5 GHz	dB	—	—	0.7
	DC - 1 GHz	dB	—	—	0.7
	DC - 2 GHz	dB	—	—	0.8
	DC - 4 GHz	dB	—	—	1.0
Isolation (SW-226)	DC - 0.5 GHz	dB	53	—	—
	DC - 1 GHz	dB	48	—	—
	DC - 2 GHz	dB	40	—	—
	DC - 4 GHz	dB	25	—	—
Isolation (SW-227)	DC - 0.5 GHz	dB	55	—	—
	DC - 1 GHz	dB	50	—	—
	DC - 2 GHz	dB	40	—	—
	DC - 4 GHz	dB	35	—	—
Isolation (SW-228)	DC - 0.5 GHz	dB	50	—	—
	DC - 1 GHz	dB	42	—	—
	DC - 2 GHz	dB	32	—	—
	DC - 4 GHz	dB	22	—	—
VSWR (SW-226)	DC - 0.5 GHz	Ratio	—	—	1.2:1
	DC - 1 GHz	Ratio	—	—	1.4:1
	DC - 2 GHz	Ratio	—	—	1.6:1
	DC - 4 GHz	Ratio	—	—	2.3:1
VSWR (SW-227)	DC - 0.5 GHz	Ratio	—	—	1.2:1
	DC - 1 GHz	Ratio	—	—	1.4:1
	DC - 2 GHz	Ratio	—	—	1.6:1
	DC - 4 GHz	Ratio	—	—	2.0:1
VSWR (SW-228)	DC - 0.5 GHz	Ratio	—	—	1.2:1
	DC - 1 GHz	Ratio	—	—	1.2:1
	DC - 2 GHz	Ratio	—	—	1.3:1
	DC - 4 GHz	Ratio	—	—	1.9:1
Trise, Tfall ⁵	10% to 90% RF, 90% to 10% RF	nS	—	3	—
Ton, Toff ⁵	50% control to 90% RF, 50% control to 10% RF	nS	—	6	—
Transients ⁵ (SW-226,SW-227)	In-Band	mV	—	30	—
Transients ⁵ (SW-228)	In-Band	mV	—	10	—

4. See MIL-STD-883 for environmental screening options.

5. Faster switching speed can be achieved with enhanced driver waveform.

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Electrical Specifications (continued): $T_A = -55^{\circ}\text{C}$ to $+85^{\circ}\text{C}$, $V_c = 0\text{ V} / -5\text{ V}$, $Z_0 = 50\ \Omega$

Parameter	Test Conditions	Units	Min.	Typ.	Max.
Input P1dB	0.5 - 4 GHz, 0 / -5 VDC	dBm	—	27	—
	0.05 GHz, 0 / -5 VDC	dBm	—	21	—
	0.5 - 4 GHz, 0 / -8 VDC	dBm	—	33	—
	0.05 GHz, 0 / -8 VDC	dBm	—	26	—
IP2	For two-tone input power up to +13 dBm				
	0.5 - 4 GHz 0.05 GHz	dBm dBm	— —	68 62	— —
IP3	For two-tone input power up to +13 dBm				
	0.5 - 4 GHz 0.05 GHz	dBm dBm	— —	46 40	— —
Control Current	$ V_c = 0$ to 0.2 V	μA	—	—	20
		μA	—	110	—
		μA	—	—	600
		μA	—	50	—
		μA	—	—	300

Handling Procedures

Please observe the following precautions to avoid damage:

Static Sensitivity

Gallium Arsenide Integrated Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these devices.

SW-226 and SW-227 Truth Table ^{6,7}

Control Input				Condition of Switch, RF Common to each RF Port	
A1	B1	A2	B2	RF1	RF2
1	0	0	1	ON	OFF
0	1	1	0	OFF	ON

SW-228 Truth Table ^{6,7}

Control Input		Condition of Switch, RF Common to each RF Port	
A1	B1	RF1	RF2
1	0	ON	OFF
0	1	OFF	ON

6. 0 = 0 V to -0.2 V, 1 = -5 V to -8 V

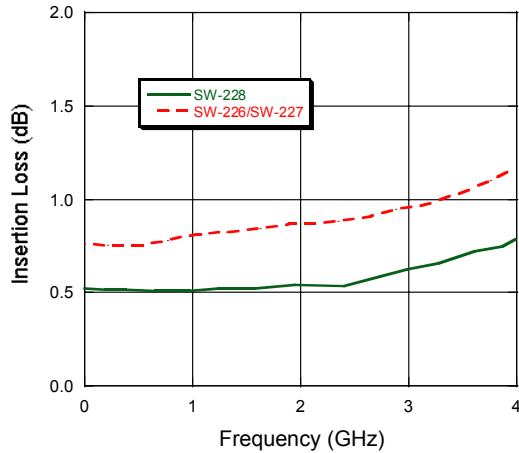
7. For the SW-227 and SW-228 only, when an RF output is "OFF" it is shorted to case ground.

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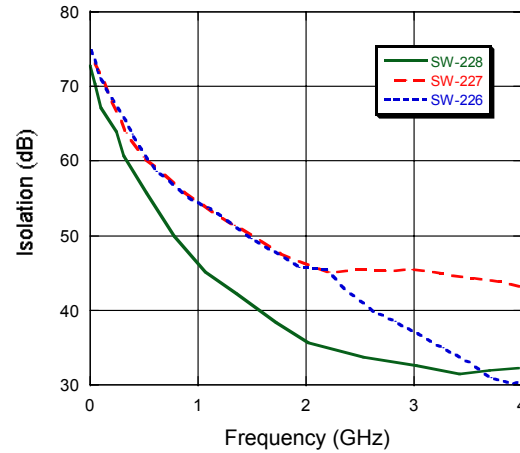
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Typical Performance Curves

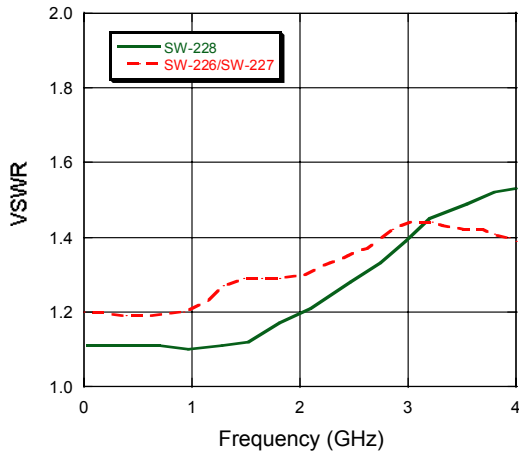
Insertion Loss



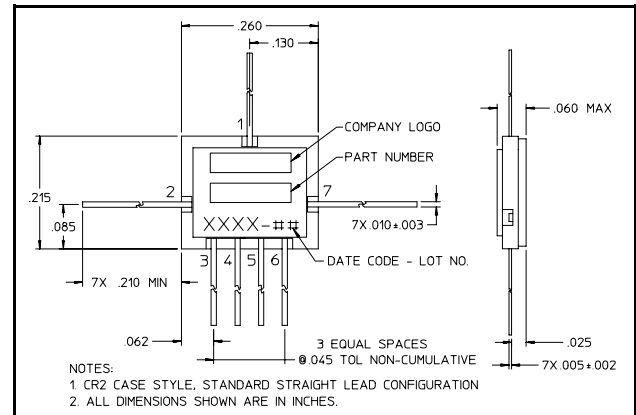
Isolation



VSWR



Lead-Free CR-2†



† Reference Application Note M538 for lead-free solder reflow recommendations.